Abstract

Radiation-emitting semiconductor component

In a radiation-emitting semiconductor component with a layer structure comprising an n-doped confinement layer (14), a p-doped confinement layer (22), and an active, photon-emitting layer (18) disposed between the n-doped confinement layer (14) and the p-doped confinement layer (22), it is provided according to the invention that the n-doped confinement layer (14) is doped with a first n-dopant (or two mutually different n-dopants) for producing high active doping and a sharp doping profile, and the active layer (18) is doped with only one second n-dopant, different from the first dopant, for improving the layer quality of the active layer (18).

Figure 1